

74LVC1G34

Single buffer

Rev. 02 — 21 May 2007

Product data sheet

1. General description

The 74LVC1G34 provides a low-power, low-voltage single buffer.

The input can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Schmitt trigger action at all inputs makes the circuit highly tolerant of slower input rise and fall times.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant inputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V).
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Multiple package options
- Specified from -40°C to $+85^{\circ}\text{C}$ and -40°C to $+125^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package				Version
	Temperature range	Name	Description		
74LVC1G34GW	−40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm		SOT353-1
74LVC1G34GV	−40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads		SOT753
74LVC1G34GM	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm		SOT886
74LVC1G34GF	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm		SOT891

4. Marking

Table 2. Marking

Type number	Marking code
74LVC1G34GW	YN
74LVC1G34GV	YN
74LVC1G34GM	YN
74LVC1G34GF	YN

5. Functional diagram

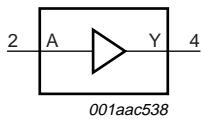


Fig 1. Logic symbol

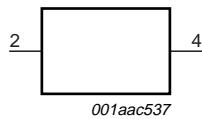


Fig 2. IEC logic symbol

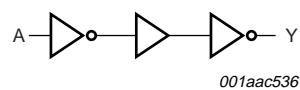


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

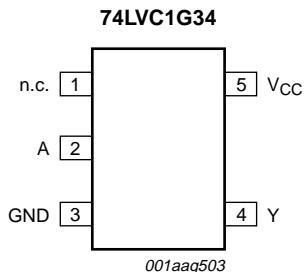


Fig 4. Pin configuration SOT353-1 and SOT753

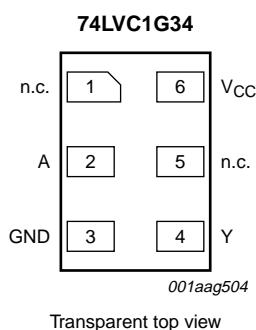


Fig 5. Pin configuration SOT886

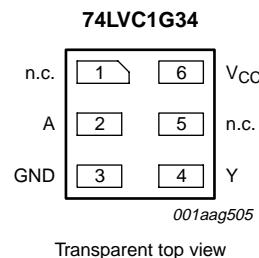


Fig 6. Pin configuration SOT891

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1/SOT753	SOT886/SOT891	
n.c.	1	1	not connected
A	2	2	data input
GND	3	3	ground (0 V)
Y	4	4	data output
n.c.	-	5	not connected
VCC	5	6	supply voltage

7. Functional description

Table 4. Function table^[1]

Input	Output
A	Y
L	L
H	H

[1] H = HIGH voltage level;
L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		[1]	-0.5	+6.5
I _{OK}	output clamping current	V _O > V _{CC} or V _O < 0 V	-	±50	mA
V _O	output voltage	Active mode	[1][2]	-0.5	V _{CC} + 0.5
		Power-down mode	[1][2]	-0.5	+6.5
I _O	output current	V _O = 0 V to V _{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[3]	-	250 mW
T _{stg}	storage temperature		-65	+150	°C

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		1.65	-	5.5	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage	Active mode	0	-	V _{CC}	V _O
		V _{CC} = 0 V; Power-down mode	0	-	5.5	V _O
T _{amb}	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
T_{amb} = -40 °C to +85 °C[1]							
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	V	
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V	
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	-	-	V	
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	V	
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V	
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V	
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V	
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = -100 μA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V	
		I _O = -4 mA; V _{CC} = 1.65 V	1.2	1.54	-	V	
		I _O = -8 mA; V _{CC} = 2.3 V	1.9	2.15	-	V	
		I _O = -12 mA; V _{CC} = 2.7 V	2.2	2.50	-	V	
		I _O = -24 mA; V _{CC} = 3.0 V	2.3	2.62	-	V	
		I _O = -32 mA; V _{CC} = 4.5 V	3.8	4.11	-	V	
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V	-	-	0.10	V	
		I _O = 4 mA; V _{CC} = 1.65 V	-	0.07	0.45	V	
		I _O = 8 mA; V _{CC} = 2.3 V	-	0.12	0.30	V	
		I _O = 12 mA; V _{CC} = 2.7 V	-	0.17	0.40	V	
		I _O = 24 mA; V _{CC} = 3.0 V	-	0.33	0.55	V	
		I _O = 32 mA; V _{CC} = 4.5 V	-	0.39	0.55	V	
I _I	input leakage current	V _{CC} = 0 V to 5.5 V; V _I = 5.5 V or GND	[2]	-	±0.1	±5	μA
I _{OFF}	power-off leakage current	V _{CC} = 0 V; V _I or V _O = 5.5 V	-	±0.1	±10	μA	
I _{CC}	supply current	V _{CC} = 1.65 V to 5.5 V; I _O = 0 A; V _I = 5.5 V or GND	-	0.1	10	μA	
ΔI _{CC}	additional supply current	V _{CC} = 2.3 V to 5.5 V; V _I = V _{CC} - 0.6 V; I _O = 0 A	[2]	-	5	500	μA
C _I	input capacitance	V _{CC} = 3.3 V; V _I = GND to V _{CC}	-	4	-	pF	
T_{amb} = -40 °C to +125 °C							
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	V	
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V	
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	-	-	V	
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	V	
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V	
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V	
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V	

Table 7. Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 µA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	0.95	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.7	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	1.9	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.0	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V	-	-	0.10	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.70	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.60	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.80	V
I _I	input leakage current	V _{CC} = 0 V to 5.5 V; V _I = 5.5 V or GND	-	-	±100	µA
I _{OFF}	power-off leakage current	V _{CC} = 0 V; V _I or V _O = 5.5 V	-	-	±200	µA
I _{CC}	supply current	V _{CC} = 1.65 V to 5.5 V; I _O = 0 A; V _I = 5.5 V or GND	-	-	200	µA
ΔI _{CC}	additional supply current	V _{CC} = 2.3 V to 5.5 V; V _I = V _{CC} - 0.6 V; I _O = 0 A	-	-	5000	µA

[1] All typical values are measured at T_{amb} = 25 °C.[2] These typical values are measured at V_{CC} = 3.3 V.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t_{pd}	propagation delay A to Y; see Figure 7	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[2]					
			1.0	4.0	8.6	1.0	11.0	ns
			0.5	2.6	4.4	0.5	5.6	ns
			0.5	2.3	4.5	0.5	5.6	ns
			0.5	2.0	4.1	0.5	5.2	ns
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC}; V_{CC} = 3.3 \text{ V}$	[3]	-	15	-	-	pF

[1] Typical values are measured at $T_{amb} = 25 \text{ }^{\circ}\text{C}$ and $V_{CC} = 1.8 \text{ V}, 2.5 \text{ V}, 2.7 \text{ V}, 3.3 \text{ V}$, and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

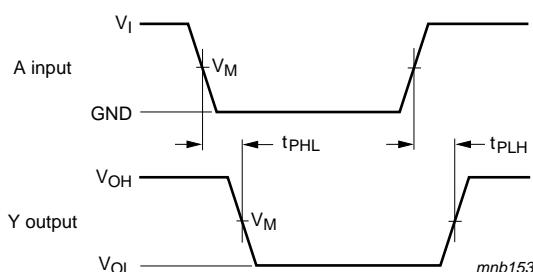
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



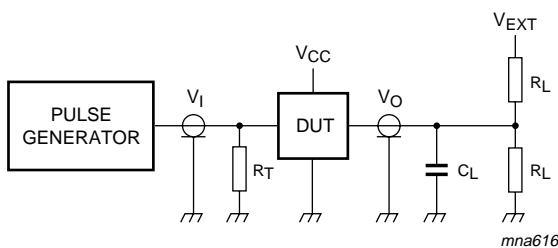
Measurement points are given in [Table 9](#).

V_{OL} and V_{OH} are typical output voltage drops that occur with the output load.

Fig 7. The data input (A) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

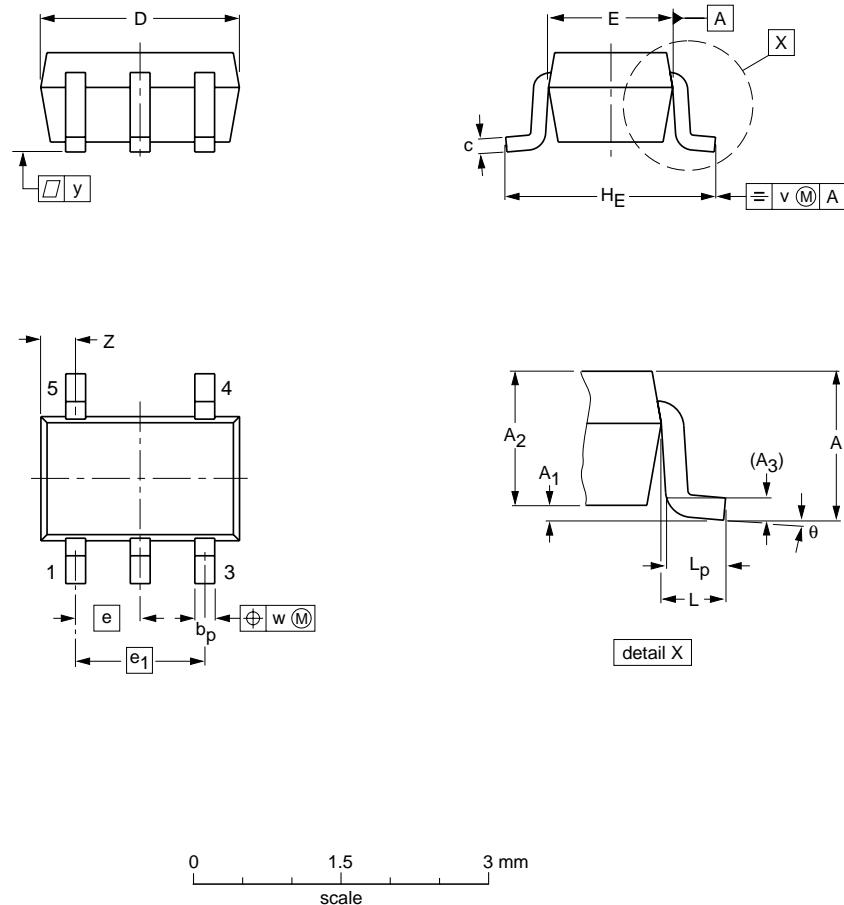
Fig 8. Load circuitry for switching times**Table 10. Test data**

Supply voltage	Load			V_{EXT}	
V_{CC}	V_I	$t_r = t_f$	C_L	R_L	t_{PLH}, t_{PHL}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

**DIMENSIONS (mm are the original dimensions)**

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	H _E	L	L _p	v	w	y	Z ⁽¹⁾	θ
mm	1.1	0.1	1.0	0.15	0.30	0.25	2.25	1.35	0.65	1.3	2.25	0.425	0.46	0.3	0.1	0.1	0.60	7°

Note

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			00-09-01 03-02-19

Fig 9. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

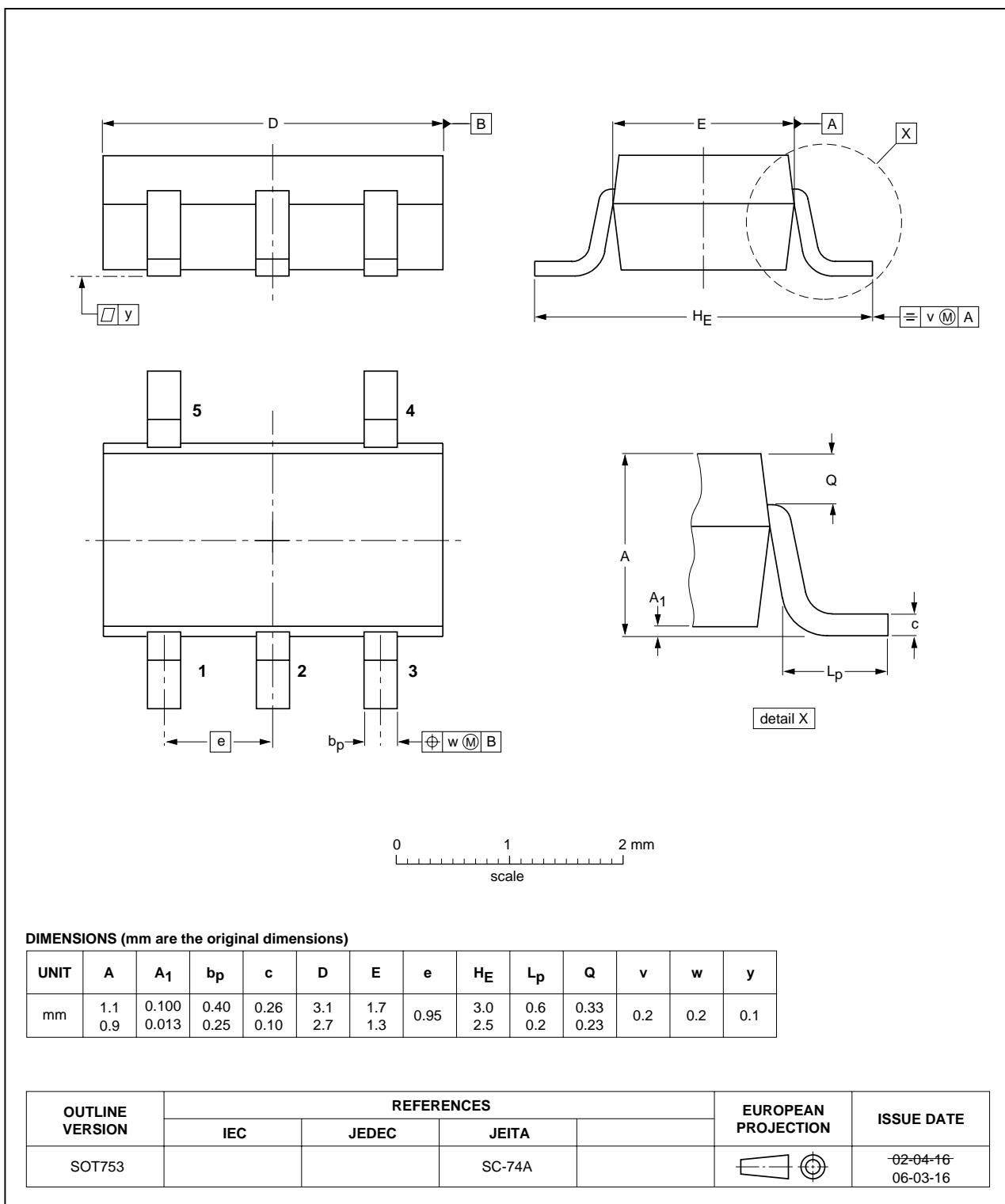
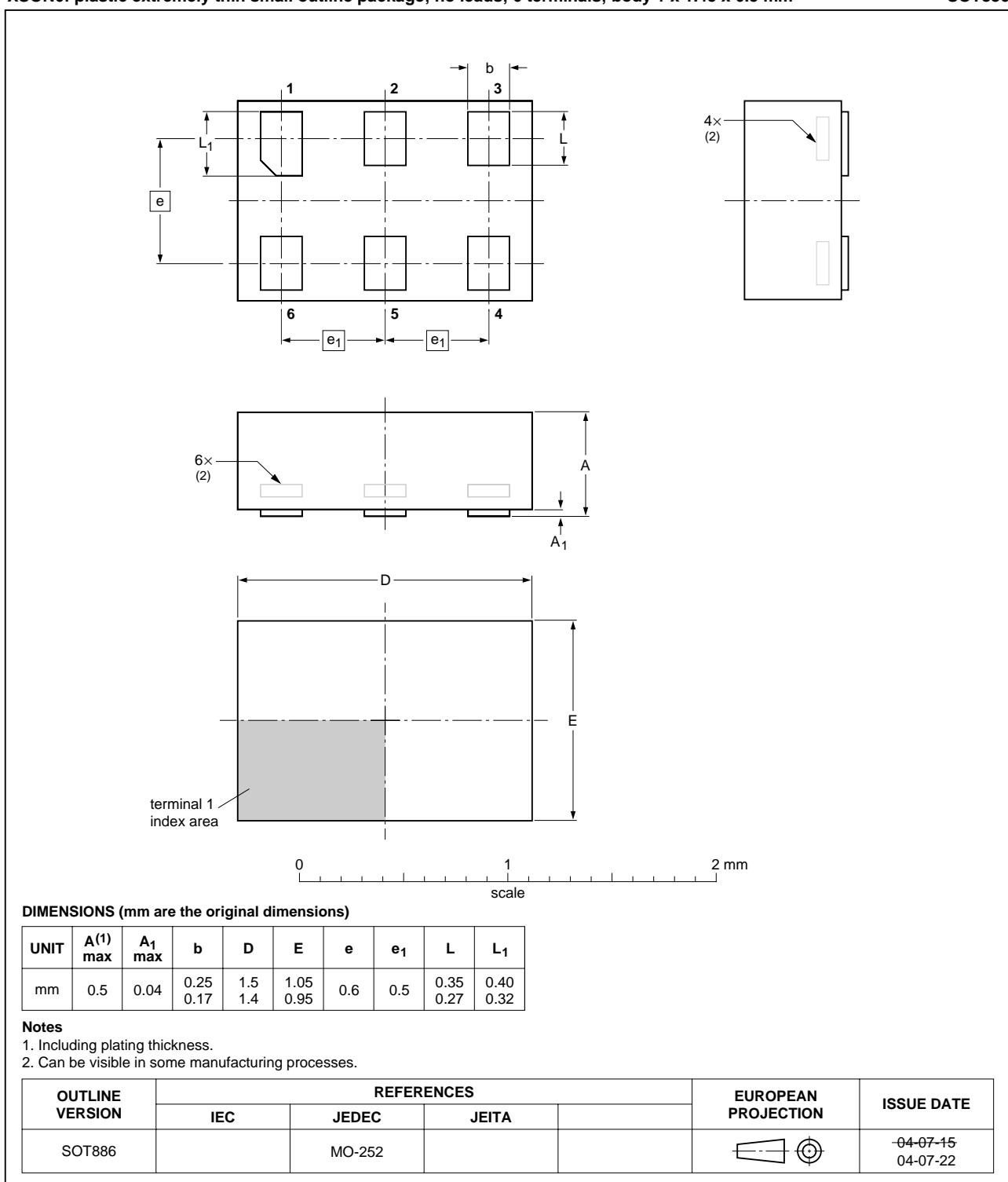


Fig 10. Package outline SOT753 (SC-74A)

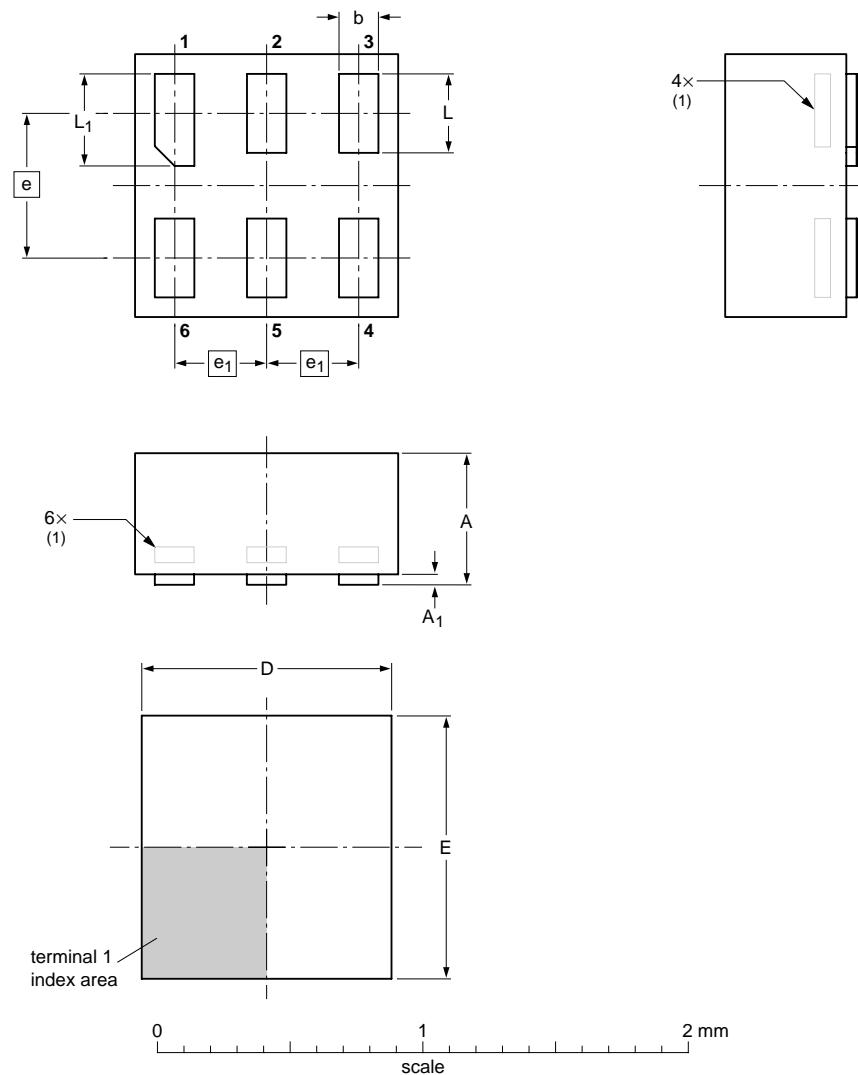
XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

**Fig 11. Package outline SOT886 (XSON6)**

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

**DIMENSIONS (mm are the original dimensions)**

UNIT	A max	A ₁ max	b	D	E	e	e ₁	L	L ₁
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35 0.27	0.35 0.27	0.40 0.32

Note

1. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						05-04-06 07-05-15

Fig 12. Package outline SOT891 (XSON6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G34_2	20070521	Product data sheet	-	74LVC1G34_1
Modifications:	<ul style="list-style-type: none">The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.Legal texts have been adapted to the new company name where appropriate.Added type number 74LVC1G34GF (XSON6/SOT891 package)<u>Section 10 "Static characteristics"</u>: Changed: Conditions for input leakage and supply current.			
74LVC1G34_1	20051107	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Document identifier: 74LVC1G34_2



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помошь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помошь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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